

LN66L

GaAs Infrared Light Emitting Diode

For optical control systems

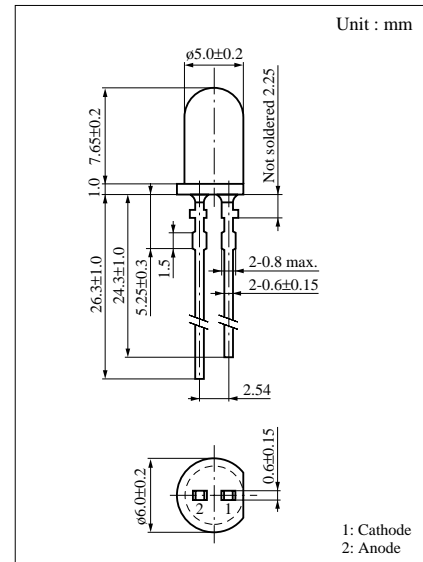
■ Features

- High-power output, high-efficiency : $P_O = 8$ mW (typ.)
- Emitted light spectrum suited for silicon photodetectors
- Good radiant power output linearity with respect to input current
- Wide directivity : $\theta = 25$ deg. (typ.)
- Transparent epoxy resin package
- Long lead-wire type

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Power dissipation	P_D	160	mW
Forward current (DC)	I_F	100	mA
Pulse forward current	I_{FP}^*	1.5	A
Reverse voltage (DC)	V_R	3	V
Operating ambient temperature	T_{opr}	-25 to +85	°C
Storage temperature	T_{stg}	-40 to +100	°C

* f = 100 Hz, Duty cycle = 0.1 %

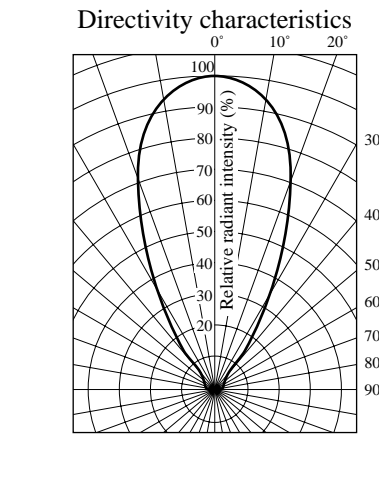
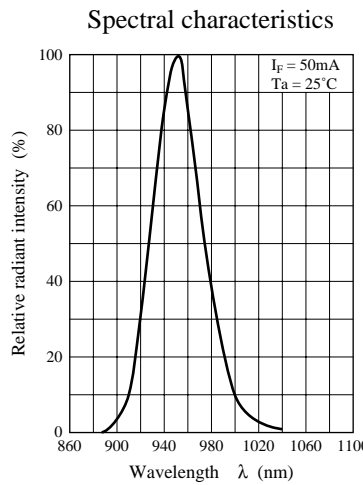
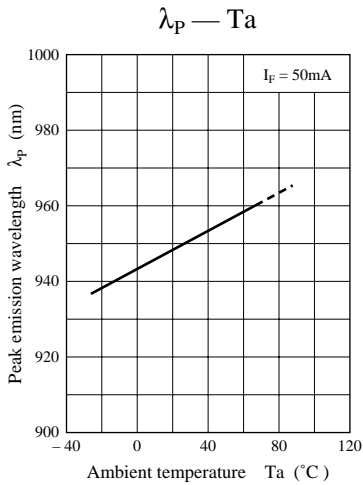
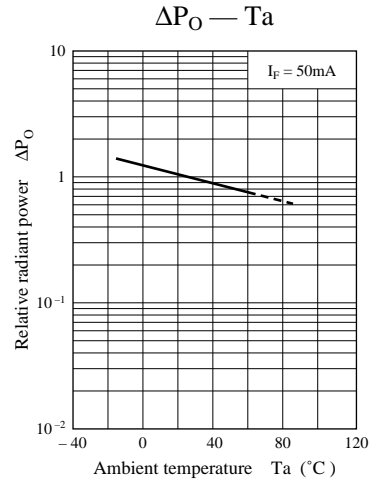
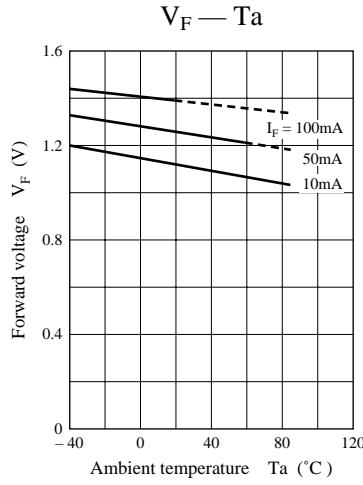
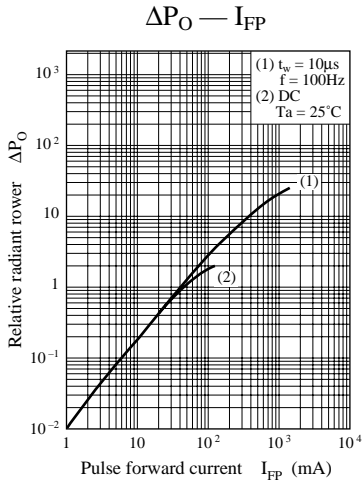
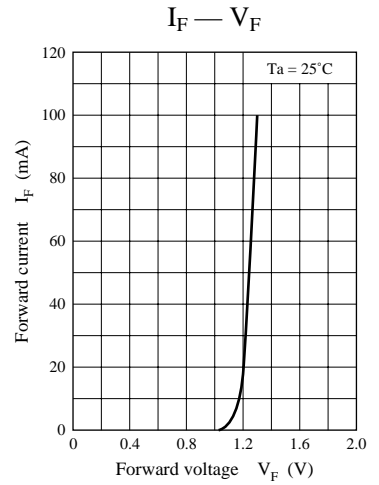
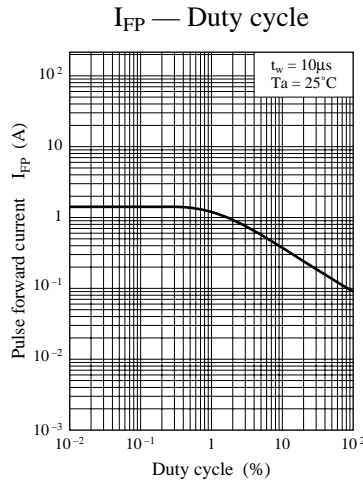
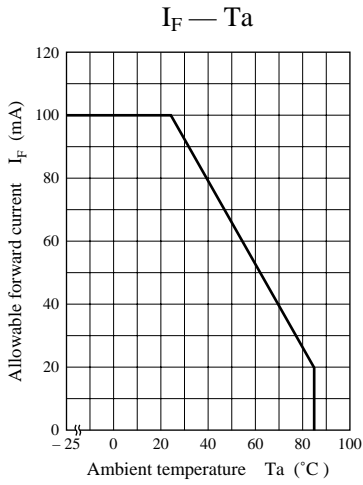


■ Electro-Optical Characteristics (Ta = 25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Radiant power	P_O^*	$I_F = 50$ mA	5	8		mW
Peak emission wavelength	λ_p	$I_F = 50$ mA		950		nm
Spectral half band width	$\Delta\lambda$	$I_F = 50$ mA		50		nm
Forward voltage (DC)	V_F	$I_F = 100$ mA		1.3	1.6	V
Reverse current (DC)	I_R	$V_R = 3$ V			10	μ A
Capacitance between pins	C_t	$V_R = 0$ V, f = 1 MHz		35		pF
Half-power angle	θ	The angle in which radiant intensity is 50%		25		deg.

* P_O Classifications

Class	R	S
P_O (mW)	5 to 8	>7



Frequency characteristics

